

# FQH90N15 / FQA90N15

## N-Channel Power MOSFET

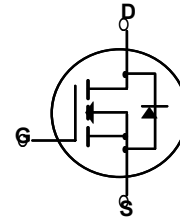
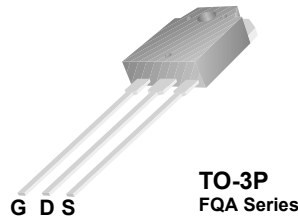
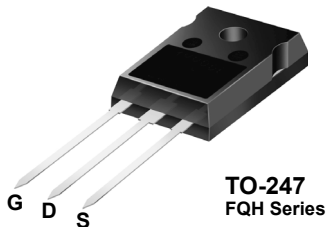
### Features

- 90A, 150V,  $R_{DS(on)} = 0.018\Omega @ V_{GS} = 10V$
- Low gate charge (typical 220 nC)
- Low  $C_{rss}$  (typical 200 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating

### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching for DC/DC converters, and DC motor control, uninterrupted power supply.



### Absolute Maximum Ratings

Symbol	Parameter	FQH90N15/FQA90N15	Unit
$V_{DSS}$	Drain-Source Voltage	150	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	90 63.5	A A
$I_{DM}$	Drain Current - Pulsed (Note 1)	360	A
$V_{GSS}$	Gate-Source voltage	$\pm 25$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	1400	mJ
$I_{AR}$	Avalanche Current (Note 1)	90	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	37.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	375 2.5	W W/°C
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	°C
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Min.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.4	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQH90N15	FQH90N15	TO-247	--	--	30
FQA90N15	FQA90N15	TO-3P	--	--	30
FQA90N15	FQA90N15_F109	TO-3PN	--	--	30

## Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

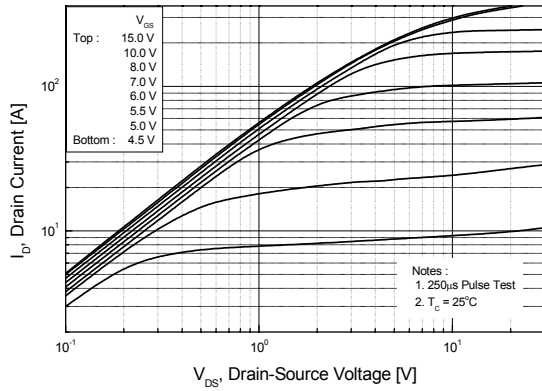
Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	150	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C	--	0.15	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 150V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 120V, T <sub>C</sub> = 150°C	--	--	1 10	μA μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25V, V <sub>DS</sub> = 0V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25V, V <sub>DS</sub> = 0V	--	--	-100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0	--	4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 45A	--	0.014	0.018	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40V, I <sub>D</sub> = 45A (Note 4)	--	68	--	S
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	--	6700	8700	pF
C <sub>oss</sub>	Output Capacitance		--	1400	1800	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	200	260	pF
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 75V, I <sub>D</sub> = 90A R <sub>G</sub> = 25Ω	--	105	220	ns
t <sub>r</sub>	Turn-On Rise Time		--	760	1500	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	470	950	ns
t <sub>f</sub>	Turn-Off Fall Time		(Note 4, 5)	--	410	830
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 120V, I <sub>D</sub> = 90A V <sub>GS</sub> = 10V	--	220	285	nC
Q <sub>gs</sub>	Gate-Source Charge		--	43	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		(Note 4, 5)	--	110	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	90	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	360	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 90A	--	--	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 90A di/dt = 100A/μs (Note 4)	--	175	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	0.97	--	μC

### NOTES:

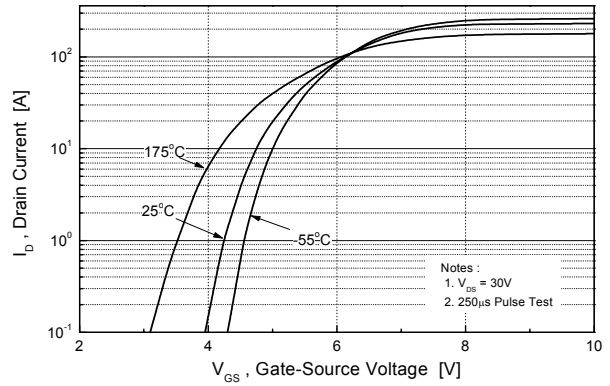
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 0.29mH, I<sub>AS</sub> = 90A, V<sub>DD</sub> = 25V, R<sub>G</sub> = 25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 90A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

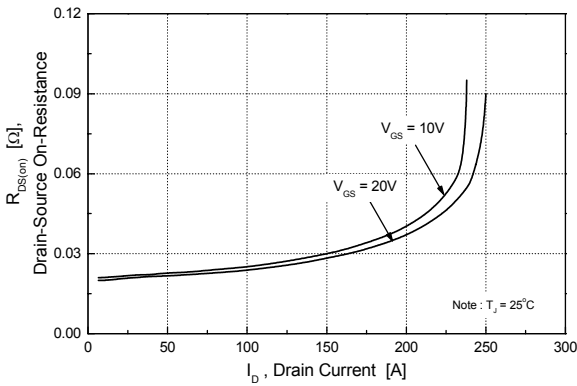
**Figure 1. On-Region Characteristics**



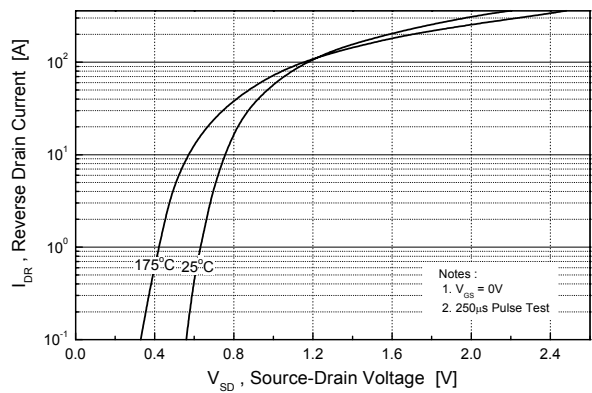
**Figure 2. Transfer Characteristics**



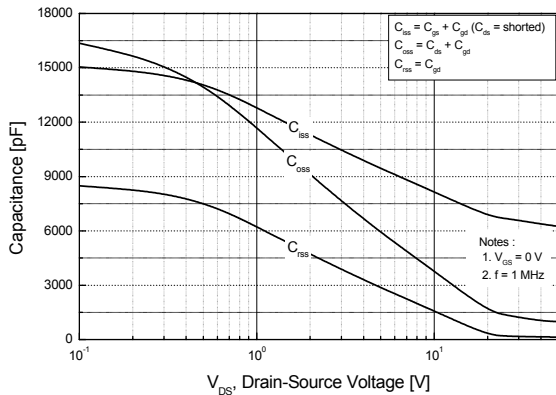
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



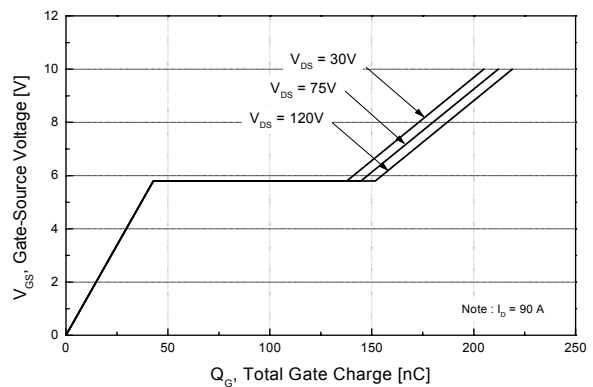
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current**



**Figure 5. Capacitance Characteristics**

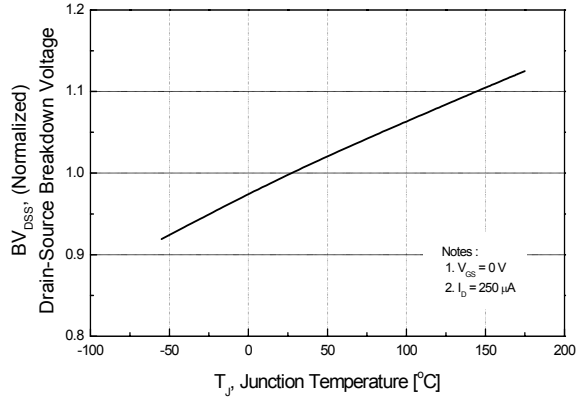


**Figure 6. Gate Charge Characteristics**

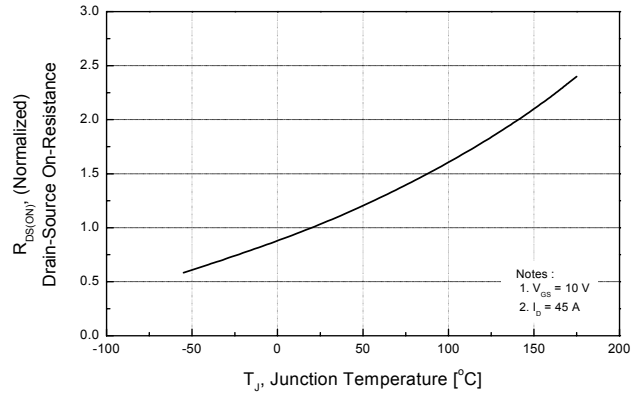


### Typical Performance Characteristics (Continued)

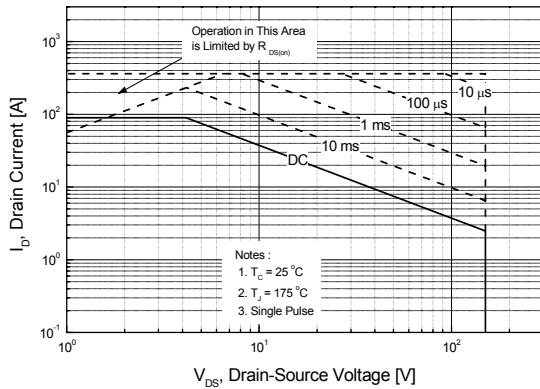
**Figure 7. Breakdown Voltage Variation vs. Temperature**



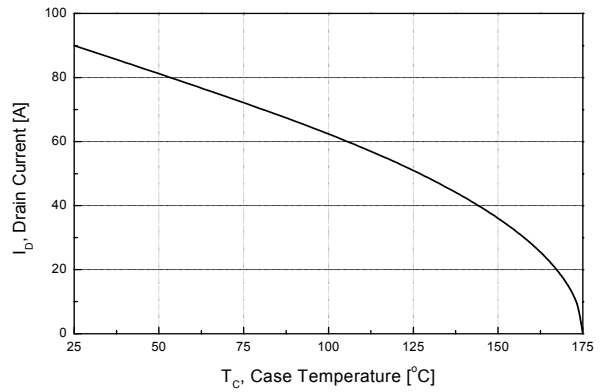
**Figure 8. On-Resistance Variation vs. Temperature**



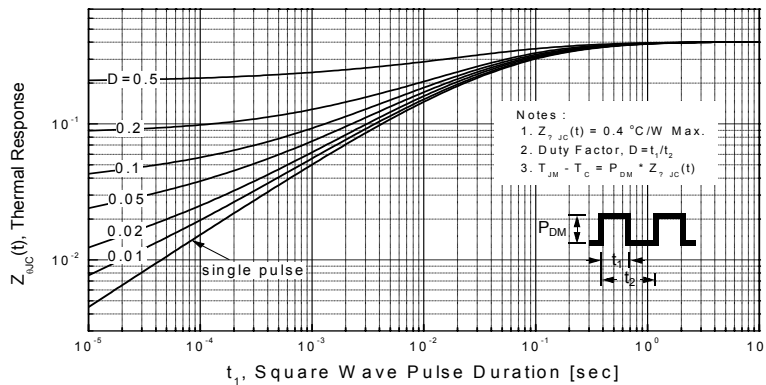
**Figure 9. Maximum Safe Operating Area**



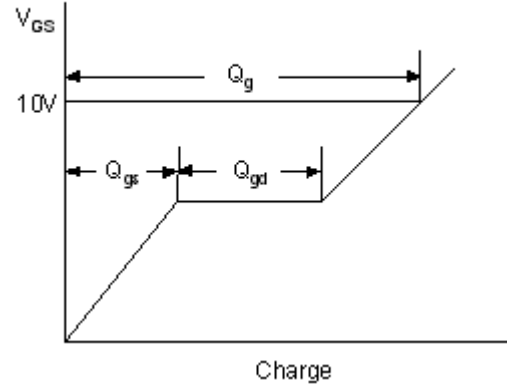
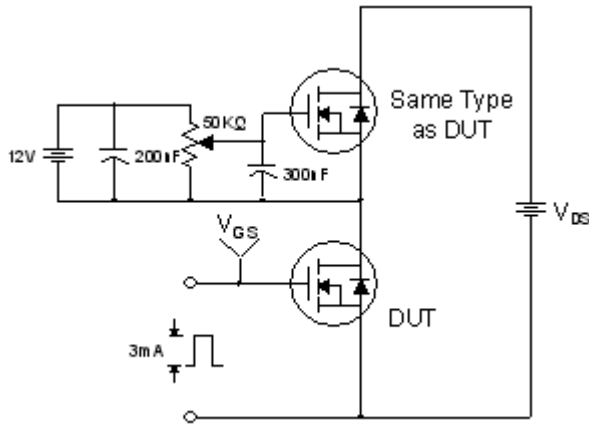
**Figure 10. Maximum Drain Current vs. Case Temperature**



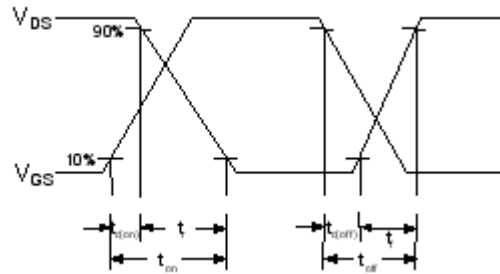
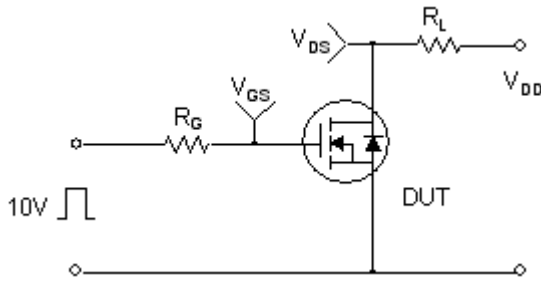
**Figure 11. Transient Thermal Response Curve**



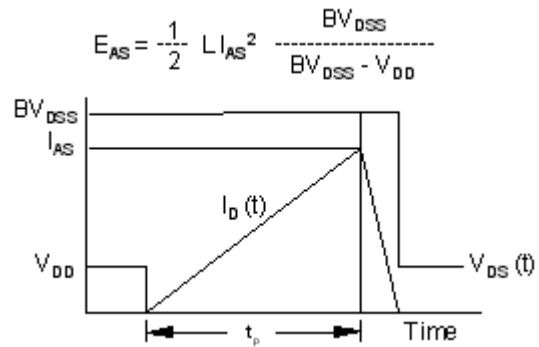
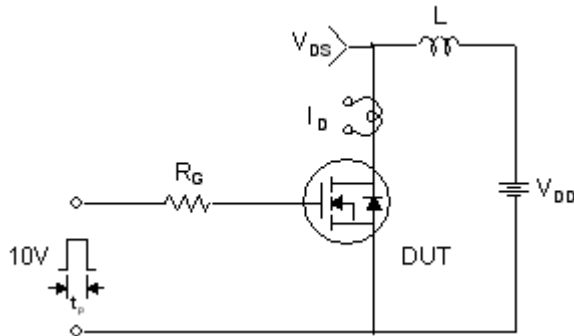
**Gate Charge Test Circuit & Waveform**



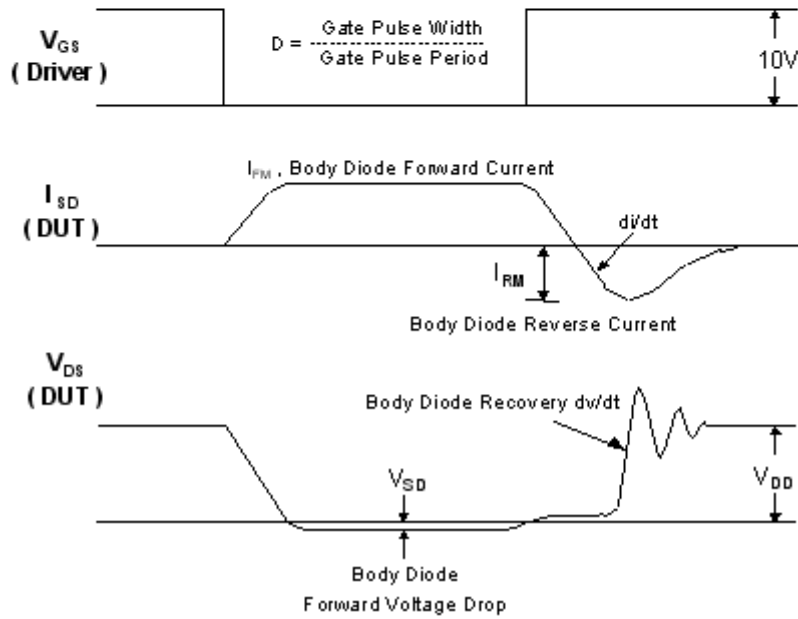
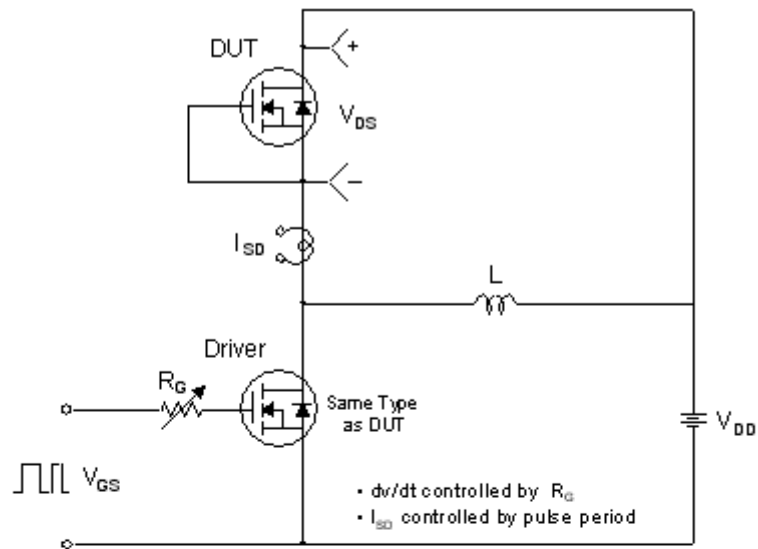
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**



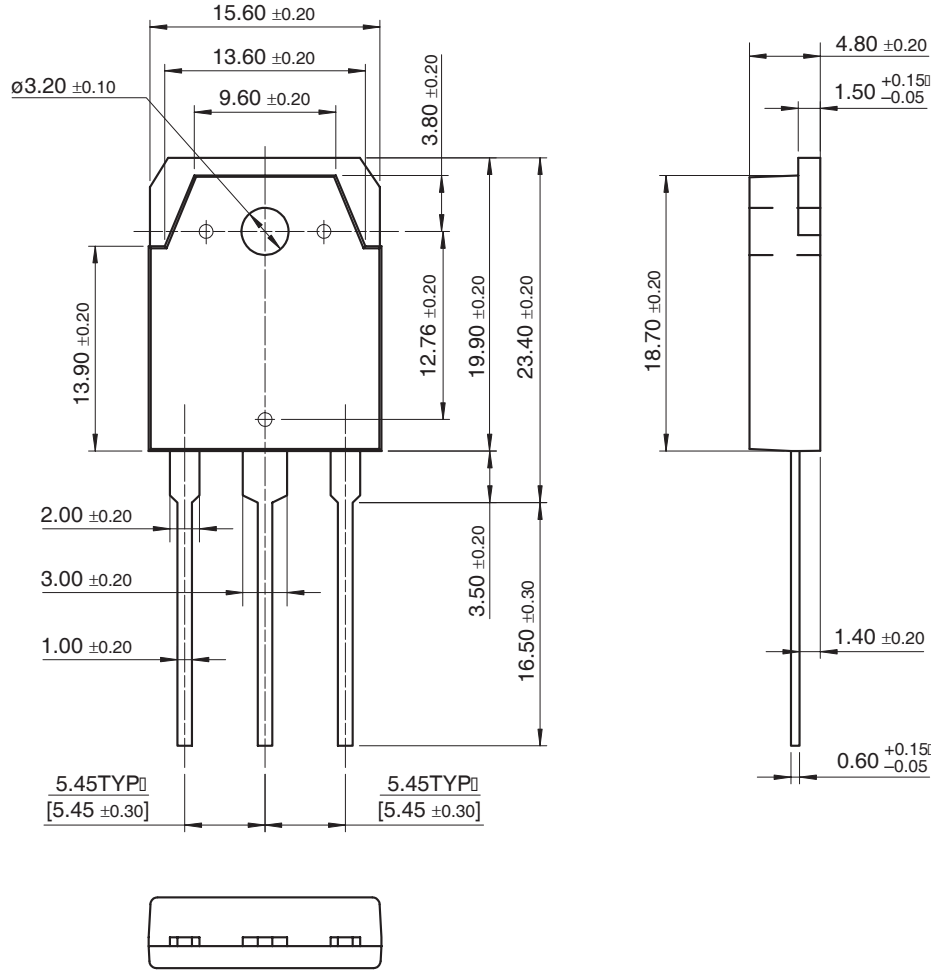
Peak Diode Recovery dv/dt Test Circuit & Waveforms





**Mechanical Dimensions** (Continued)

**TO-3P**

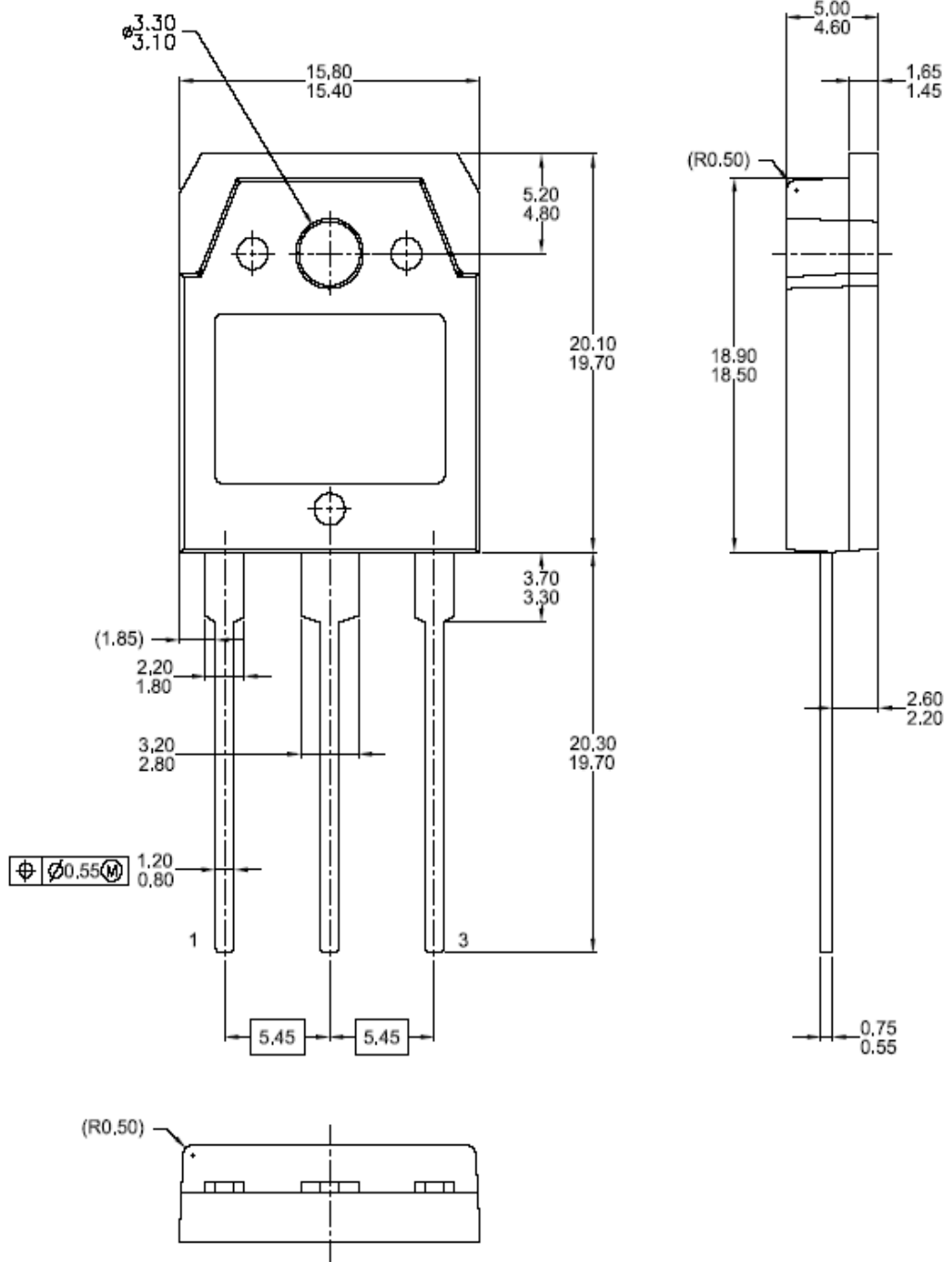


Dimensions in Millimeters



**Mechanical Dimensions** (Continued)

**TO-3PN**



Dimensions in Millimeters

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CROSSVOLT <sup>™</sup>	i-Lo <sup>™</sup>	POP <sup>™</sup>	SuperSOT <sup>™</sup> -3	
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Rev. I20